Philips Semiconductors

Product specification

Rectifier diodes Schottky barrier

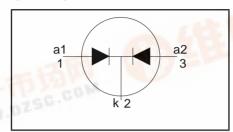
PBYL2525CT, PBYL2525CTB series

FEATURES

• Low forward volt drop

- Fast switching
- Reverse surge capability
- High thermal cycling performance
- · Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 20 \text{ V}/25 \text{ V}$$
 $I_{O(AV)} = 25 \text{ A}$
 $V_F \le 0.43 \text{ V}$

GENERAL DESCRIPTION

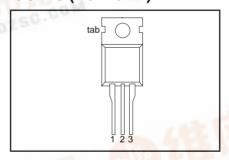
Dual schottky rectifier diodes intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYL2525CT series is supplied in the SOT78 (TO220AB) conventional leaded package. The PBYL2525CTB series is supplied in the SOT404 surface mounting package.

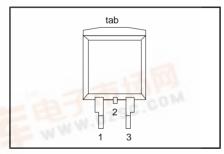
PINNING

PIN	DESCRIPTION		
1	gate		
2	drain ¹		
3	source		
tab	drain		

SOT78 (TO220AB)



SOT404



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MIN. MAX.		UNIT
V _{RRM}	Peak repetitive reverse	PBYL25 PBYL25	-	20CT 20CTB 20	25CT 25CTB 25	V
KKM	voltage		444	-1.71	1701	
V_{RWM}	Working peak reverse voltage		EE	20	25	V
V_R	Continuous reverse voltage	T _{mb} ≤ 120 °C	- 1	20	25	V
I _{O(AV)}	Average rectified output current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{mb} \le 119$ °C	-	25		А
I _{FRM}	Repetitive peak forward current per diode	square wave; $\delta = 0.5$; $T_{mb} \le 119 ^{\circ}\text{C}$	-	2	5	Α
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM(max)}}$	-		35 50	A A
I _{RRM}	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T _{i max}	-	1		Α
T _j	Operating junction temperature	, max	-	15	50	°C
为 PDF	Storage temperature		- 65	5 175		°C

1/ It is not possible to make connection to pin 2 of the SOT404 package.

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PBYL2525CT, PBYL2525CTB series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
		per diode	-	-	3	K/W
R _{th i-a}	to mounting base Thermal resistance junction	both diodes SOT78 package, in free air	-	60	-	K/W K/W
	to ambient	SOT404 package, pcb mounted, minimum footprint, FR4 board	-	50	-	K/W

ELECTRICAL CHARACTERISTICS

All characteristics are per diode at T_i = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage	$I_F = 12.5 \text{ A}; T_j = 150^{\circ}\text{C}$	-	0.36	0.43	V
		$I_F = 12.5 \text{ A}$; $I_i = 125 ^{\circ}\text{C}$	-	0.38	0.47	V
		$I_{\rm F} = 25 \text{A}; T_{\rm i} = 125 ^{\circ} \text{C}$	-	0.5	0.62	V
		$I_{\rm F} = 25 \mathrm{A}$	-	0.54	0.66	V
I _R	Reverse current	$\dot{V}_R = V_{RWM}$	-	1	5	mΑ
		$V_R = V_{RWM}$; $T_j = 100^{\circ}C$	-	20	30	mΑ
C_d	Junction capacitance	$V_R = 5 \text{ V}; \text{ f} = 1 \text{ MHz}, T_j = 25 ^{\circ}\text{C} \text{ to } 125 ^{\circ}\text{C}$	-	600	-	pF

PBYL2525CT, PBYL2525CTB series

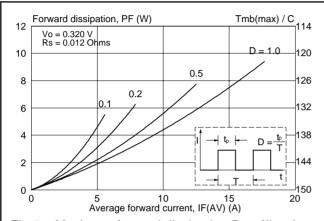


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

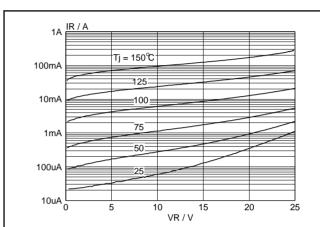


Fig.4. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

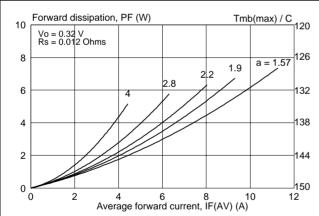


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form factor $= I_{F(RMS)} / I_{F(AV)}$.

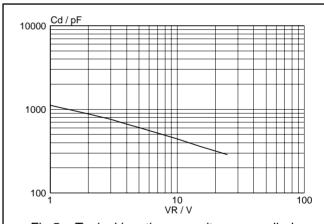


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125 °C.

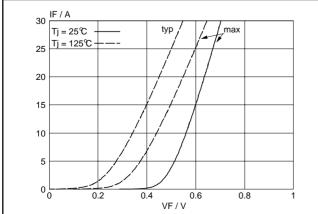


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

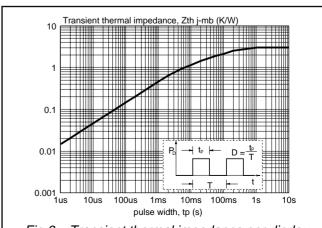
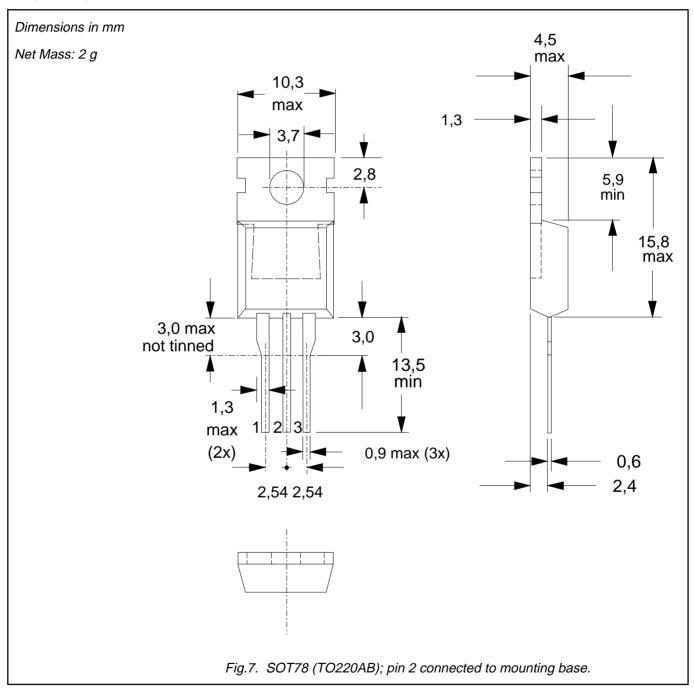


Fig.6. Transient thermal impedance per diode; $Z_{th j-mb} = f(t_p)$.

PBYL2525CT, PBYL2525CTB series

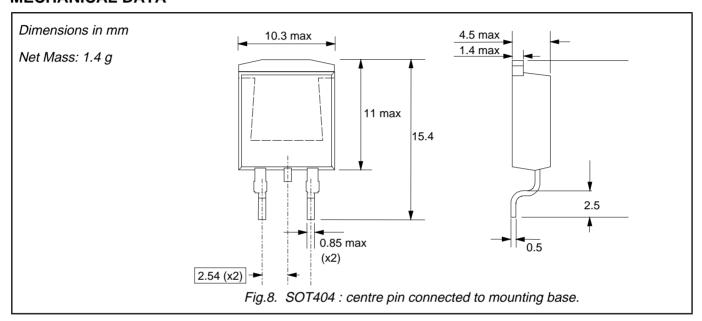
MECHANICAL DATA



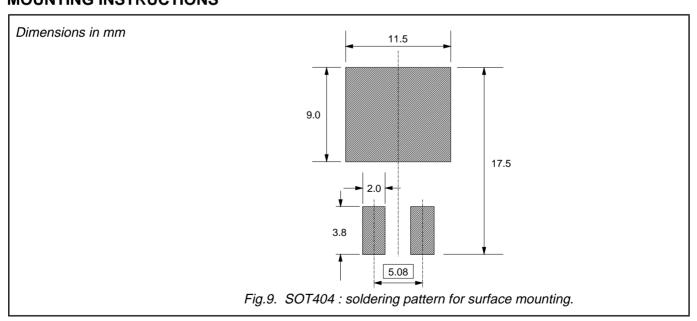
- Refer to mounting instructions for SOT78 (TO220) envelopes.
 Epoxy meets UL94 V0 at 1/8".

PBYL2525CT, PBYL2525CTB series

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes
1. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier	diodes
Schottky	barrier

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DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification This data sheet contains preliminary data; supplementary data may be published I				
Product specification	This data sheet contains final product specifications.			
I the Marian and the same				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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